

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-23. (Cancelled).

24. (Currently amended) An apparatus ~~for etching a substrate material~~ comprising:  
a chamber;  
a support located within the chamber ~~to support the substrate material~~;  
a quartz plate supported by the support;  
a high frequency energy source;  
a first gas supply providing a first gas, the first etchant gas comprising  $C_xF_y$  molecules, x and y being integers;  
a first inlet for introducing the first gas into the chamber to form a first plasma gas when energized by the high frequency energy source;  
a second gas supply providing a second gas, the second etchant gas comprising  $SpFq$  molecules, p and q being integers; and  
a second inlet for introducing the second gas into the chamber to form a second plasma gas when energized by the high frequency energy source;  
wherein the first and second plasma gas are used to etch the quartz plate.

25. (Original) The apparatus of claim 24, further comprising a flow controller for controlling the amount of the first and second etchant gases entering the chamber.

26. (Currently amended) The apparatus of claim 24, wherein the first gas ~~is~~ comprises carbon fluoride and the second gas ~~is sulfur~~ comprises sulfur fluoride.